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PS9308L, PS9308L2

Data Sheet

R08DS0048EJ0100

Rev.1.00

Aug 31, 2011

2.0 A OUTPUT CURRENT, HIGH CMR,
 IGBT GATE DRIVE, 6-PIN SDIP PHOTOCOUPLER

DESCRIPTION

The PS9308L and PS9308L2 are optical coupled isolators containing a GaAlAs LED on the input side and a photo diode, a signal processing circuit and a power output transistor on the output side on one chip.

The PS9308L and PS9308L2 are in 6-pin plastic SDIP (Shrink Dual In-line Package). The PS9308L2 has 8 mm creepage distance. The mount area of 6-pin plastic SDIP is half size of 8-pin DIP.

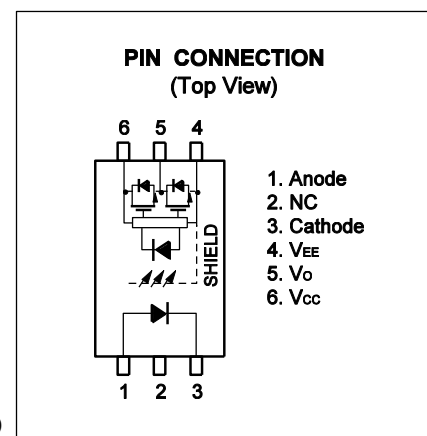
The PS9308L and PS9308L2 are designed specifically for high common mode transient immunity (CMR) and high switching speed. It is suitable for driving IGBTs and MOS FETs.

The PS9308L is lead bending type (Gull-wing) for surface mounting.

The PS9308L2 is lead bending type for long creepage distance (Gull-wing) for surface mount.

FEATURES

- Long creepage distance (8 mm MIN.: PS9308L2)
- Half size of 8-pin DIP
- Peak output current (2.0 A MAX., 1.0 A MIN.)
- High speed switching (t_{PLH} , t_{PHL} = 0.25 μ S MAX.)
- UVLO (Under Voltage Lock Out) protection with hysteresis
- High common mode transient immunity (CM_H , CM_L = ± 25 kV/ μ S MIN.)
- Embossed tape product : PS9308L-E3, PS9308L2-E3 : 2 000 pcs/reel
- Pb-Free product
- Safety standards
 - UL approved: No. E72422
 - CSA approved: No. CA 101391 (CA5A, CAN/CSA-C22.2 60065, 60950)
 - SEMKO approved: No. 1115598
 - DIN EN60747-5-2 (VDE0884 Part2) approved: No. 40024069 (Option)

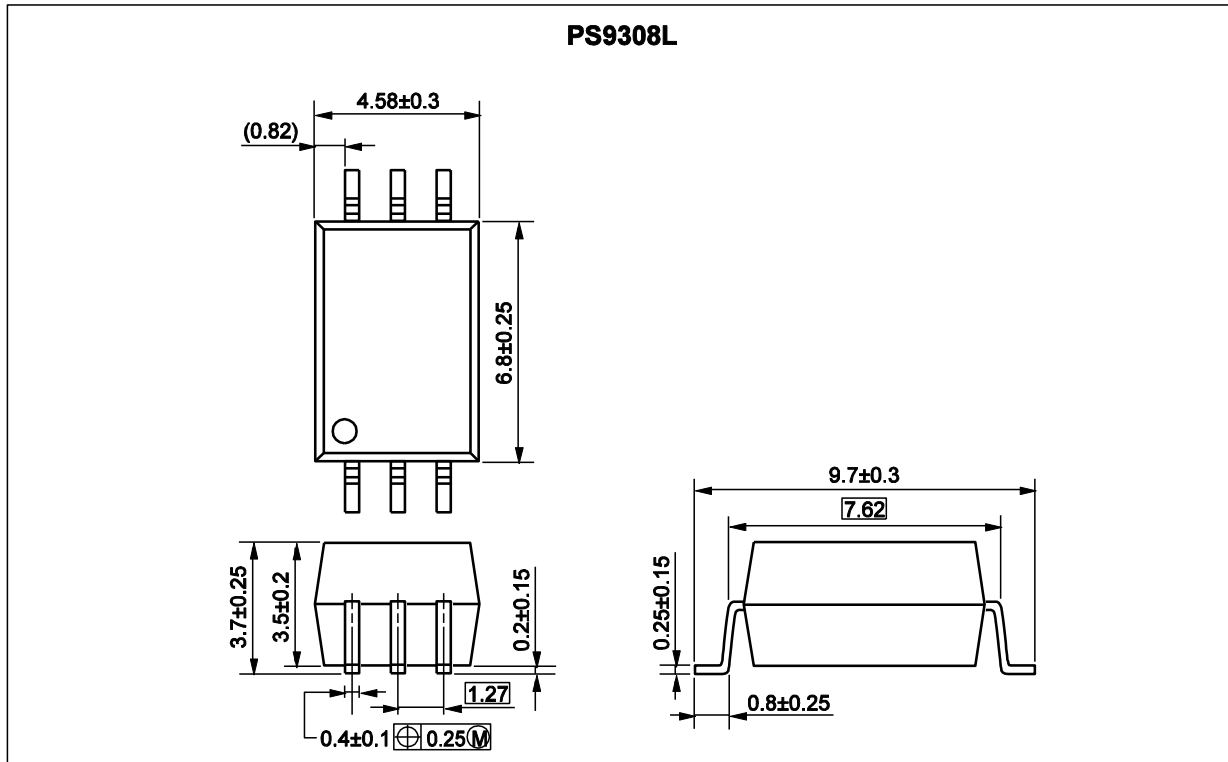


APPLICATIONS

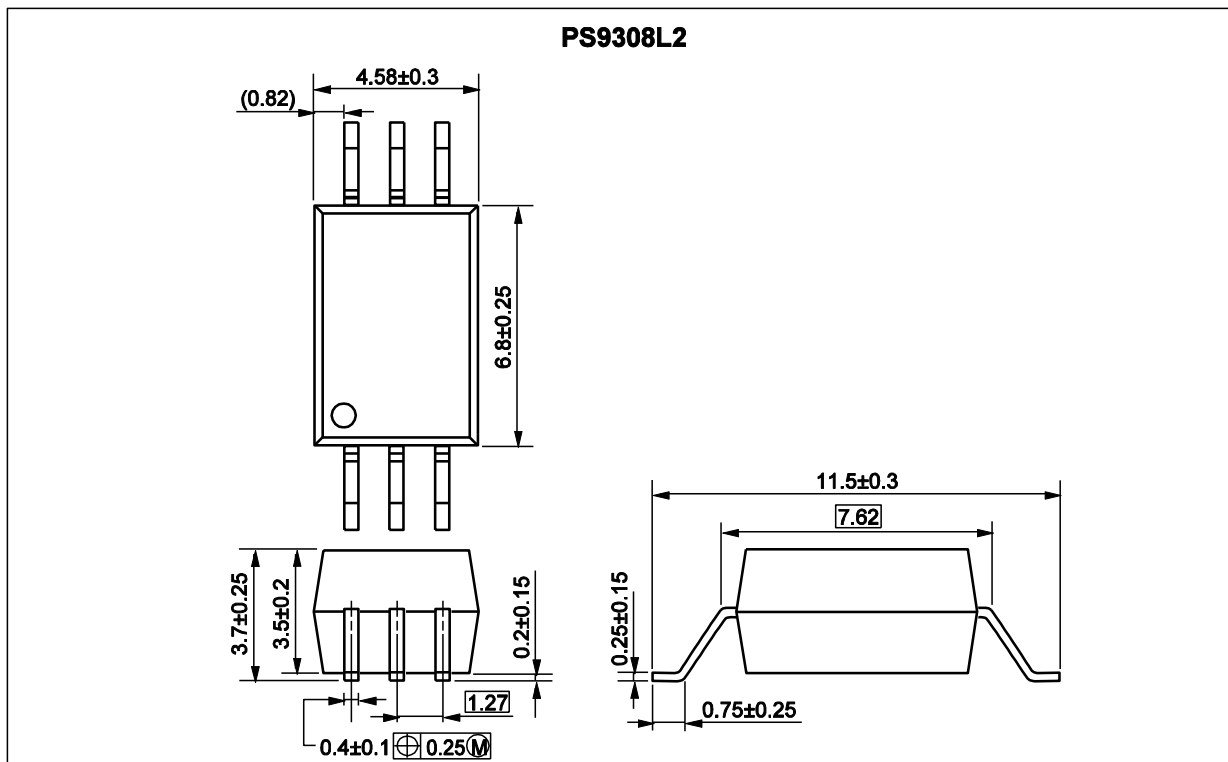
- IGBT, Power MOS FET Gate Driver
- Industrial inverter
- IH (Induction Heating)

PACKAGE DIMENSIONS (UNIT: mm)

Lead Bending Type (Gull-wing) For Surface Mount



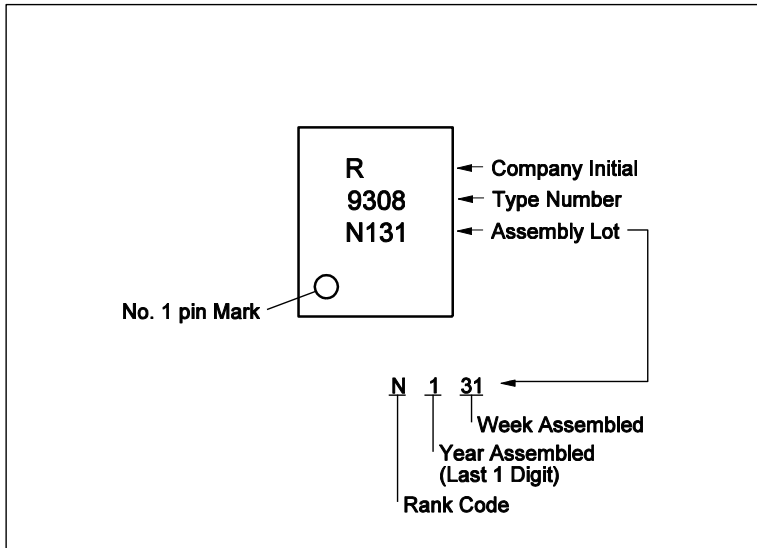
Lead Bending Type (Gull-wing) For Long Creepage Distance (Surface Mount)



PHOTOCOUPLER CONSTRUCTION

Parameter	PS9308L	PS9308L2
Air Distance (MIN.)	7 mm	8 mm
Outer Creepage Distance (MIN.)	7 mm	8 mm
Isolation Distance (MIN.)	0.4 mm	0.4 mm

MARKING EXAMPLE



ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number ^{*1}
PS9308L	PS9308L-AX	Pb-Free (Ni/Pd/Au)	20 pcs (Tape 20 pcs cut)	Standard products (UL, CSA, SEMKO approved)	PS9308L
PS9308L-E3	PS9308L-E3-AX		Embossed Tape 2 000 pcs/reel		
PS9308L2	PS9308L2-AX		20 pcs (Tape 20 pcs cut)	DIN EN60747-5-2 (VDE0884 Part2) approved (Option)	PS9308L
PS9308L2-E3	PS9308L2-E3-AX		Embossed Tape 2 000 pcs/reel		
PS9308L-V	PS9308L-V-AX		20 pcs (Tape 20 pcs cut)	PS9308L2	
PS9308L-V-E3	PS9308L-V-E3-AX		Embossed Tape 2 000 pcs/reel		
PS9308L2-V	PS9308L2-V-AX		20 pcs (Tape 20 pcs cut)	PS9308L2	
PS9308L2-V-E3	PS9308L2-V-E3-AX		Embossed Tape 2 000 pcs/reel		

Note: *1. For the application of the Safety Standard, following part number should be used.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current	I _F	25	mA
	Peak Transient Forward Current (Pulse Width < 1 μs)	I _{F (TRAN)}	1.0	A
	Reverse Voltage	V _R	5	V
Detector	High Level Peak Output Current *1	I _{OH (PEAK)}	2.0	A
	Low Level Peak Output Current *1	I _{OL (PEAK)}	2.0	A
	Supply Voltage	(V _{CC} -V _{EE})	0 to 35	V
	Output Voltage	V _O	0 to V _{CC}	V
	Power Dissipation *2	P _C	250	mW
Isolation Voltage *3	BV	5 000	Vr.m.s.	
Total Power Dissipation *4	P _T	300	mW	
Operating Frequency *5	f	50	kHz	
Operating Ambient Temperature	T _A	-40 to +110	°C	
Storage Temperature	T _{stg}	-55 to +125	°C	

Notes: *1. Maximum pulse width = 10 μs, Maximum duty cycle = 0.2%

*2. Reduced to 4.8 mW/°C at T_A = 70°C or more.

*3. AC voltage for 1 minute at T_A = 25°C, RH = 60% between input and output.
Pins 1-3 shorted together, 4-6 shorted together.

*4. Reduced to 5.4 mW/°C at T_A = 70°C or more.

*5. I_{OH (PEAK)} ≤ 2.0 A (≤ 0.3 μs), I_{OL (PEAK)} ≤ 2.0 A (≤ 0.3 μs)

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	(V _{CC} -V _{EE})	15		30	V
Forward Current (ON)	I _{F (ON)}	7	10	16	mA
Forward Voltage (OFF)	V _{F (OFF)}	-2		0.8	V
Operating Ambient Temperature	T _A	-40		110	°C

ELECTRICAL CHARACTERISTICS (at RECOMMENDED OPERATING CONDITIONS, $V_{EE} = \text{GND}$, unless otherwise specified)

Parameter		Symbol	Conditions	MIN.	TYP.* ¹	MAX.	Unit
Diode	Forward Voltage	V_F	$I_F = 10 \text{ mA}$, $T_A = 25^\circ\text{C}$	1.2	1.56	1.8	V
	Reverse Current	I_R	$V_R = 3 \text{ V}$, $T_A = 25^\circ\text{C}$			10	μA
	Input Capacitance	C_{IN}	$f = 1 \text{ MHz}$, $V_F = 0 \text{ V}$, $T_A = 25^\circ\text{C}$		30		pF
Detector	High Level Output Current	I_{OH}	$V_O = (V_{CC} - 4 \text{ V})^{*2}$	1.0	1.5		A
			$V_O = (V_{CC} - 15 \text{ V})^{*3}$	1.5			
	Low Level Output Current	I_{OL}	$V_O = (V_{EE} + 2.5 \text{ V})^{*2}$	1.0	1.5		A
			$V_O = (V_{EE} + 15 \text{ V})^{*3}$	1.5			
	High Level Output Voltage	V_{OH}	$I_O = -100 \text{ mA}^{*4}$	$V_{CC} - 3.0$	$V_{CC} - 1.3$		V
	Low Level Output Voltage	V_{OL}	$I_O = 100 \text{ mA}$		0.1	0.5	V
	High Level Supply Current	I_{CCH}	$I_F = 10 \text{ mA}$, $V_O = \text{open}$		1.2	2.0	mA
	Low Level Supply Current	I_{CCL}	$V_F = 0 \text{ to } 0.8 \text{ V}$, $V_O = \text{open}$		1.2	2.0	mA
	UVLO Threshold	V_{UVLO+}	$V_O > 5 \text{ V}$, $I_F = 10 \text{ mA}$	10.8	12.3	13.4	V
				V_{UVLO-}	9.5	11.0	
UVLO Hysteresis	$UVLO_{HYS}$		0.4	1.3			
Coupled	Threshold Input Current (L \rightarrow H)	I_{FLH}	$I_O = 0 \text{ mA}$, $V_O > 5 \text{ V}$		1.8	5.0	mA
	Threshold Input Voltage (H \rightarrow L)	V_{FHL}	$I_O = 0 \text{ mA}$, $V_O < 5 \text{ V}$	0.8			V

Notes: *1. Typical values at $T_A = 25^\circ\text{C}$.

*2. Maximum pulse width = 50 μs , Maximum duty cycle = 0.5%.

*3. Maximum pulse width = 10 μs , Maximum duty cycle = 0.2%.

*4. V_{OH} is measured with the DC load current in this testing. (Maximum pulse width = 2 ms, Maximum duty cycle = 20%)

SWITCHING CHARACTERISTICS (at RECOMMENDED OPERATING CONDITIONS, $V_{EE} = GND$, unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit	
Propagation Delay Time (L → H)	t_{PLH}	$R_g = 10 \Omega$, $C_g = 10 \text{ nF}$, $f = 10 \text{ kHz}$, Duty Cycle = 50%*2, $I_F = 10 \text{ mA}$		0.08	0.25	μs	
Propagation Delay Time (H → L)	t_{PHL}			0.10	0.25	μs	
Pulse Width Distortion (PWD)	$ t_{PHL} - t_{PLH} $				0.02	0.1	μs
Propagation Delay Time (Difference Between Any Two Products)	$t_{PHL} - t_{PLH}$			-0.1		0.1	μs
Rise Time	t_r				50		ns
Fall Time	t_f				50		ns
Common Mode Transient Immunity at High Level Output	$ CM_H $	$T_A = 25^\circ\text{C}$, $I_F = 10 \text{ mA}$, $V_{CC} = 30 \text{ V}$, $V_{CM} = 1.5 \text{ kV}$, $V_{O(MIN.)} = 26 \text{ V}$	25			$\text{kV}/\mu\text{s}$	
Common Mode Transient Immunity at Low Level Output	$ CM_L $	$T_A = 25^\circ\text{C}$, $I_F = 0 \text{ mA}$, $V_{CC} = 30 \text{ V}$, $V_{CM} = 1.5 \text{ kV}$, $V_{O(MAX.)} = 1 \text{ V}$	25			$\text{kV}/\mu\text{s}$	

Notes: *1. Typical values at $T_A = 25^\circ\text{C}$.

*2. This load condition is equivalent to the IGBT load at 1 200 V/25 A.

TEST CIRCUIT

Fig. 1 I_{OH} Test Circuit

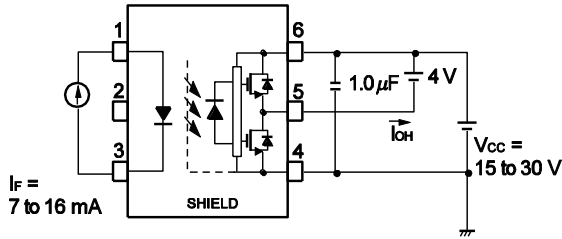


Fig. 2 I_{OL} Test Circuit

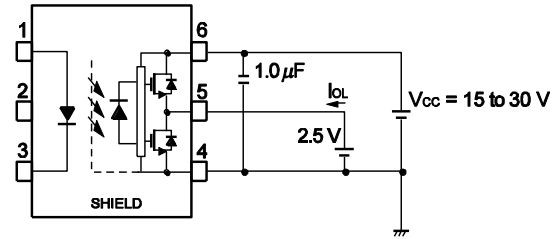


Fig. 3 V_{OH} Test Circuit

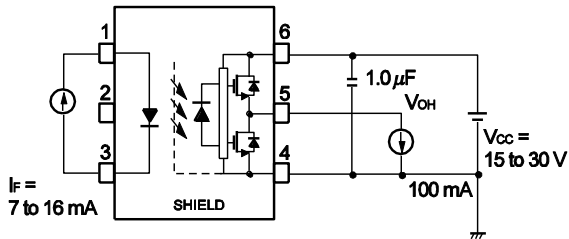


Fig. 4 V_{OL} Test Circuit

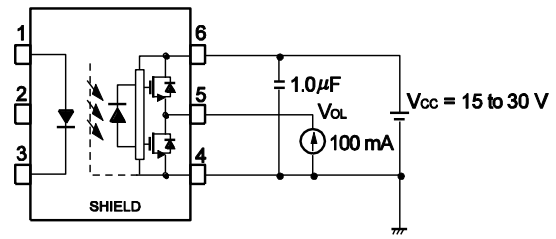


Fig. 5 UVLO Test Circuit

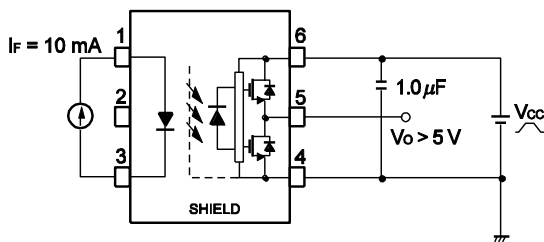


Fig. 6 I_{FLH} Test Circuit

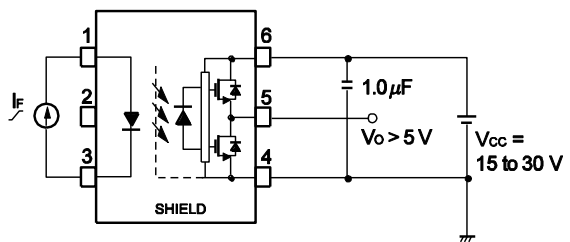


Fig. 7 t_{PLH} , t_{PHL} , t_r , t_f Test Circuit and Wave Forms

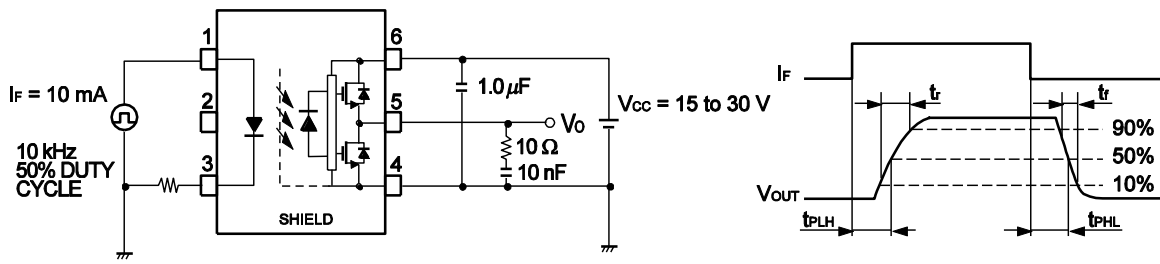
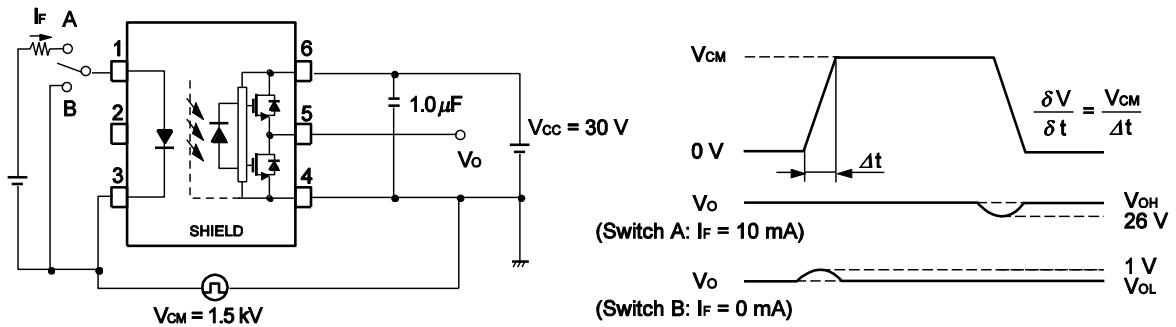
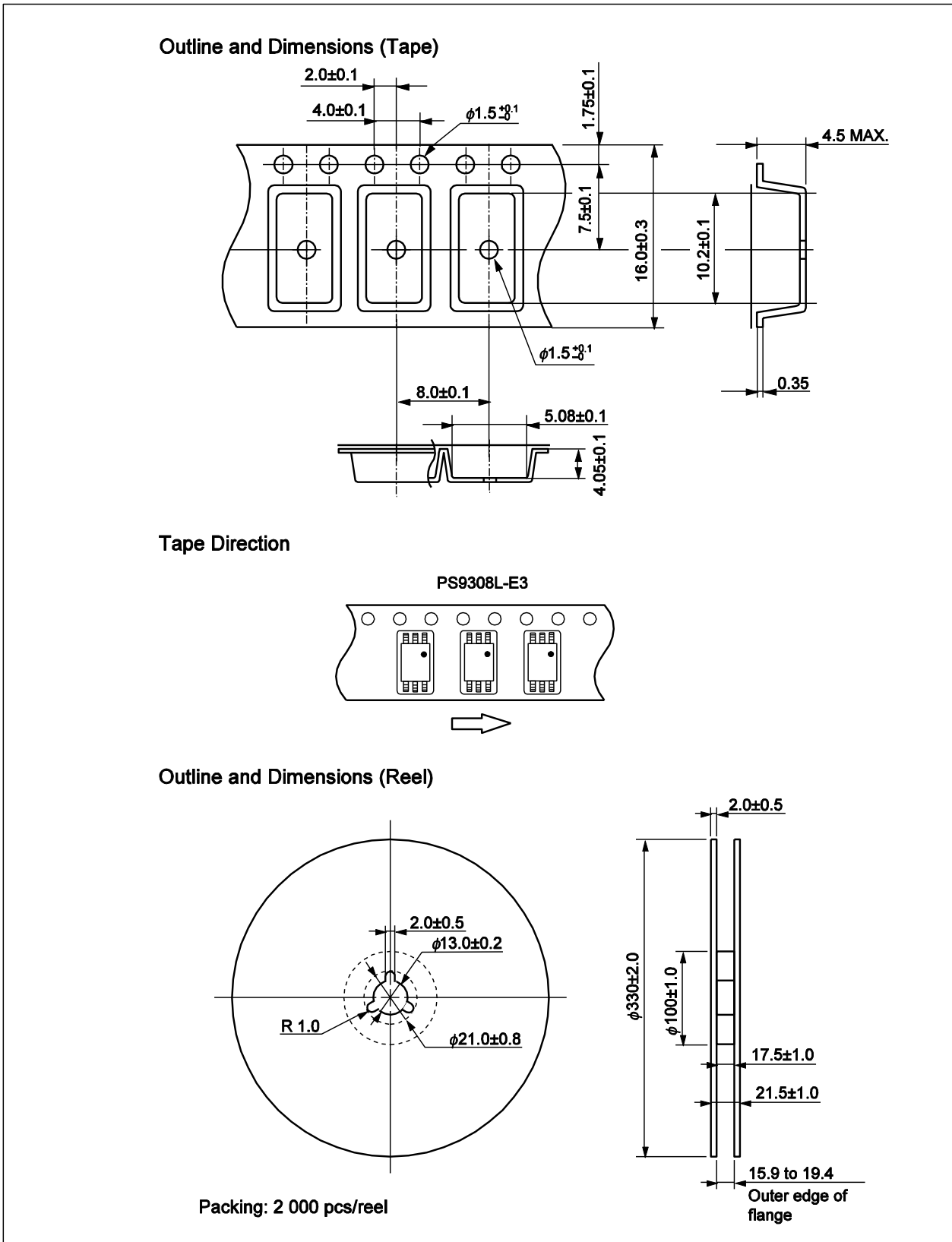


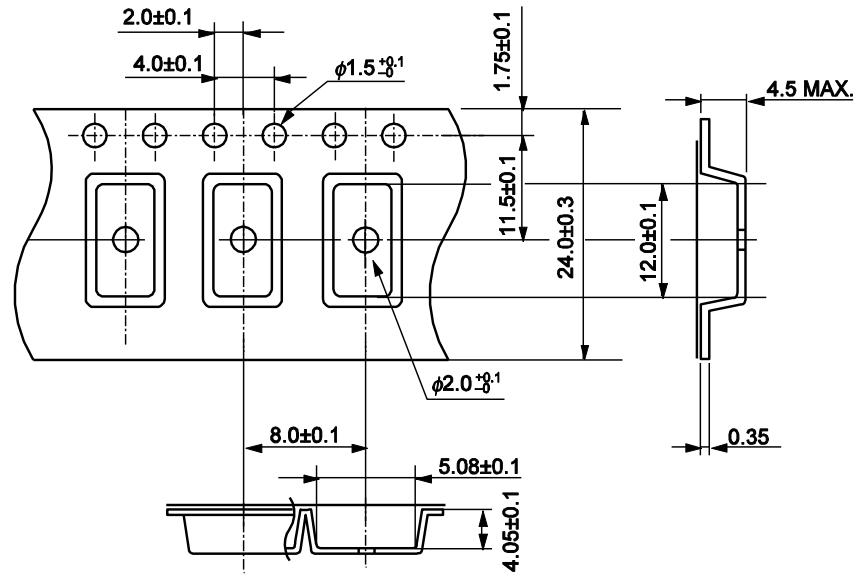
Fig. 8 CMR Test Circuit and Wave Forms



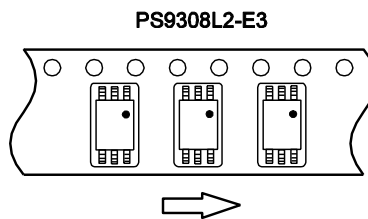
TAPING SPECIFICATIONS (UNIT: mm)



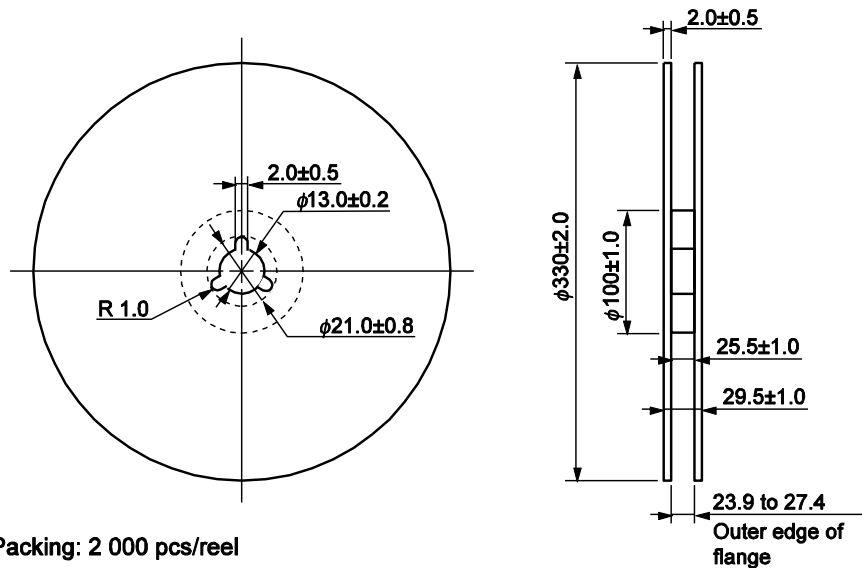
Outline and Dimensions (Tape)



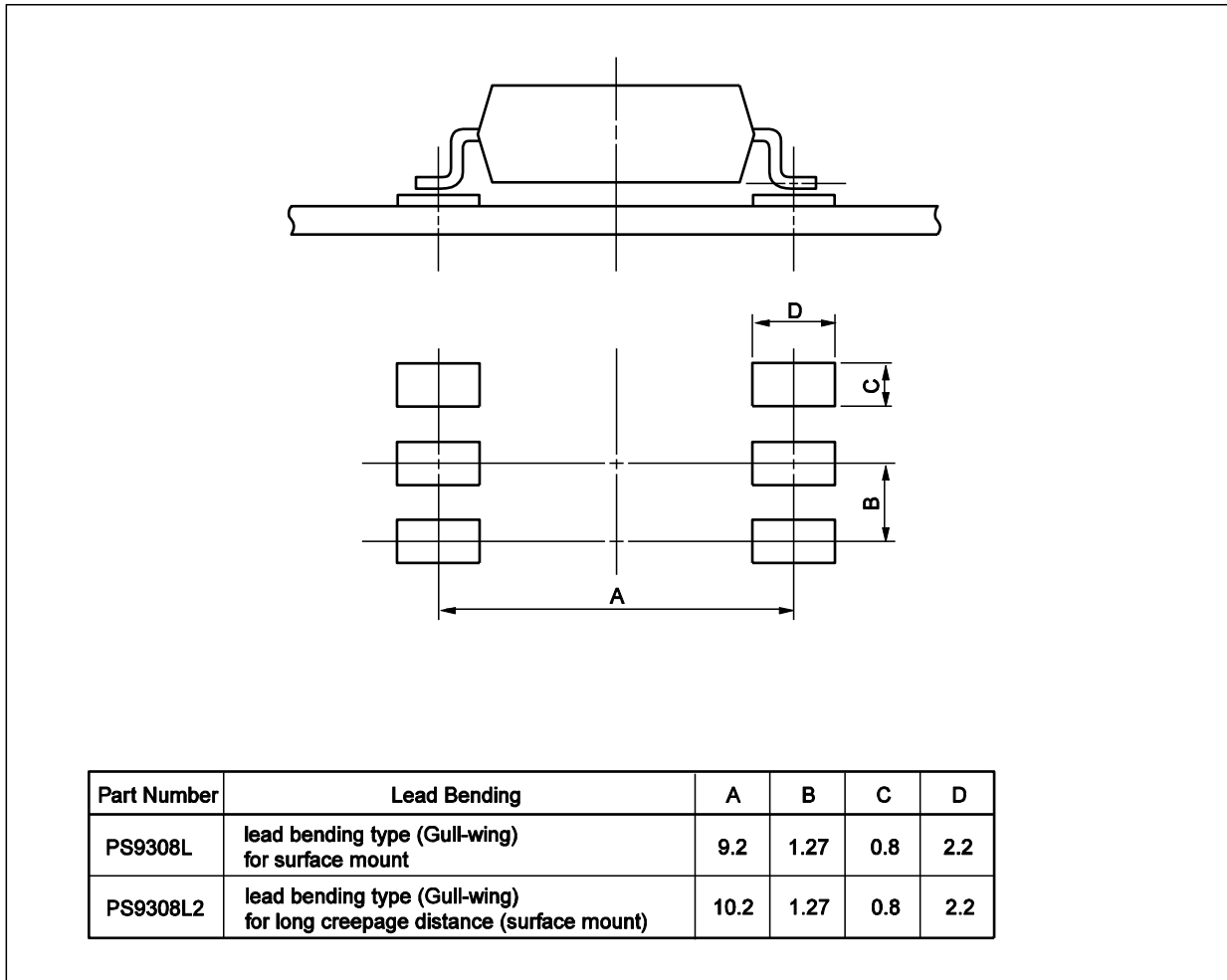
Tape Direction



Outline and Dimensions (Reel)



RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



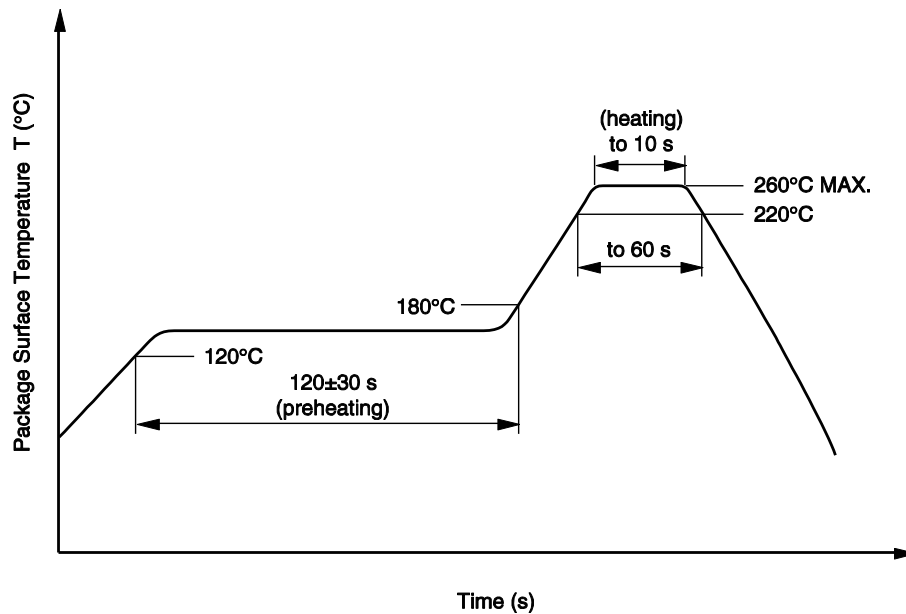
NOTES ON HANDLING (UNIT: mm)

1. Recommended soldering conditions

(1) Infrared reflow soldering

- | | |
|---|--|
| • Peak reflow temperature | 260°C or below (package surface temperature) |
| • Time of peak reflow temperature | 10 seconds or less |
| • Time of temperature higher than 220°C | 60 seconds or less |
| • Time to preheat temperature from 120 to 180°C | 120 ± 30 s |
| • Number of reflows | Three |
| • Flux | Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.) |

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

- | | |
|-------------------------|--|
| • Temperature | 260°C or below (molten solder temperature) |
| • Time | 10 seconds or less |
| • Preheating conditions | 120°C or below (package surface temperature) |
| • Number of times | One (Allowed to be dipped in solder including plastic mold portion.) |
| • Flux | Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.) |

(3) Soldering by Soldering Iron

- | | |
|--|--|
| • Peak Temperature (lead part temperature) | 350°C or below |
| • Time (each pins) | 3 seconds or less |
| • Flux | Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.) |

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead

(4) Cautions

- | | |
|----------|--|
| • Fluxes | Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent. |
|----------|--|

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

USAGE CAUTIONS

1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
2. Board designing
 - (1) By-pass capacitor of more than 1.0 μF is used between V_{CC} and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
 - (2) When designing the printed wiring board, ensure that the pattern of the IGBT collectors/emitters is not too close to the input block pattern of the photocoupler.

If the pattern is too close to the input block and coupling occurs, a sudden fluctuation in the voltage on the IGBT output side might affect the photocoupler's LED input, leading to malfunction or degradation of characteristics. (If the pattern needs to be close to the input block, to prevent the LED from lighting during the off state due to the abovementioned coupling, design the input-side circuit so that the bias of the LED is reversed, within the range of the recommended operating conditions, and be sure to thoroughly evaluate operation.)
 - (3) Pin 2 (which is an NC^{*1} pin) can either be connected directly to the GND pin on the LED side or left open. Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.

Note: *1. NC: Non-Connection (No Connection).
3. Make sure the rise/fall time of the forward current is 0.5 μs or less.
4. In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is 3 V/ μs or less.
5. Avoid storage at a high temperature and high humidity.

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/110/21	
Dielectric strength maximum operating isolation voltage	U_{IORM}	1 130	V_{peak}
Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.5 \times U_{IORM}, P_d < 5 \text{ pC}$	U_{pr}	1 695	V_{peak}
Test voltage (partial discharge test, procedure b for all devices) $U_{pr} = 1.875 \times U_{IORM}, P_d < 5 \text{ pC}$	U_{pr}	2 119	V_{peak}
Highest permissible overvoltage	U_{TR}	8 000	V_{peak}
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	CTI	175	
Material group (DIN EN 60664-1 VDE0110 Part 1)		III a	
Storage temperature range	T_{stg}	-55 to +125	$^{\circ}\text{C}$
Operating temperature range	T_A	-40 to +110	$^{\circ}\text{C}$
Isolation resistance, minimum value $V_{IO} = 500 \text{ V dc at } T_A = 25^{\circ}\text{C}$ $V_{IO} = 500 \text{ V dc at } T_A \text{ MAX. at least } 100^{\circ}\text{C}$	Ris MIN. Ris MIN.	10^{12} 10^{11}	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	T_{si}	175	$^{\circ}\text{C}$
Current (input current I_F , $P_{si} = 0$)	I_{si}	400	mA
Power (output or total power dissipation)	P_{si}	700	mW
Isolation resistance $V_{IO} = 500 \text{ V dc at } T_A = T_{si}$	Ris MIN.	10^9	Ω

Caution	GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none">• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.<ol style="list-style-type: none">1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.• Do not burn, destroy, cut, crush, or chemically dissolve the product.• Do not lick the product or in any way allow it to enter the mouth.
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Revision History	PS9308L,PS9308L2 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Aug 31, 2011	–	First edition issued

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